

August 1996

High Frequency NPN Transistor Array

Features

- Gain Bandwidth Product (f_T) >1GHz
- Power Gain 30dB (Typ) at 100MHz
- Noise Figure 3.5dB (Typ) at 100MHz
- Five Independent Transistors on a Common Substrate

Applications

- VHF Amplifiers
- Multifunction Combinations - RF/Mixer/Oscillator
- Sense Amplifiers
- Synchronous Detectors
- VHF Mixers
- IF Converter
- IF Amplifiers
- Synthesizers
- Cascade Amplifiers

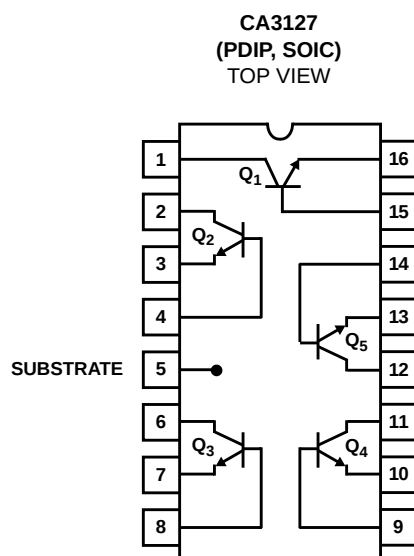
Description

The CA3127 consists of five general purpose silicon NPN transistors on a common monolithic substrate. Each of the completely isolated transistors exhibits low $1/f$ noise and a value of f_T in excess of 1GHz, making the CA3127 useful from DC to 500MHz. Access is provided to each of the terminals for the individual transistors and a separate substrate connection has been provided for maximum application flexibility. The monolithic construction of the CA3127 provides close electrical and thermal matching of the five transistors.

Ordering Information

PART NUMBER (BRAND)	TEMP. RANGE (°C)	PACKAGE	PKG. NO.
CA3127E	-55 to 125	16 Ld PDIP	E16.3
CA3127M (3127)	-55 to 125	16 Ld SOIC	M16.15
CA3127M96 (3127)	-55 to 125	16 Ld SOIC Tape and Reel	M16.15

Pinout



CA3127

Absolute Maximum Ratings

The following ratings apply for each transistor in the device

Collector-to-Emitter Voltage, V_{CEO}	15V
Collector-to-Base Voltage, V_{CBO}	20V
Collector-to-Substrate Voltage, V_{CIO} (Note 1).	20V
Collector Current, I_C	20mA

Operating Conditions

Temperature Range -55°C to 125°C

CAUTION: Stresses above those listed in "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress only rating and operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied.

NOTES:

1. The collector of each transistor of the CA3127 is isolated from the substrate by an integral diode. The substrate (Terminal 5) must be connected to the most negative point in the external circuit to maintain isolation between transistors and to provide for normal transistor action.
2. θ_{JA} is measured with the component mounted on an evaluation PC board in free air.

Thermal Information

Thermal Resistance (Typical, Note 2)	θ_{JA} (°C/W)
PDIP Package	90
SOIC Package	175
Maximum Power Dissipation, P_D (Any One Transistor).	85mW
Maximum Junction Temperature (Die)	175°C
Maximum Junction Temperature (Plastic Packages).	150°C
Maximum Storage Temperature Range	-65°C to 150°C
Maximum Lead Temperature (Soldering 10s).	300°C
(SOIC - Lead Tips Only)	

Electrical Specifications $T_A = 25^\circ\text{C}$

PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNITS
DC CHARACTERISTICS (For Each Transistor)					
Collector-to-Base Breakdown Voltage	$I_C = 10\mu\text{A}$, $I_E = 0$	20	32	-	V
Collector-to-Emitter Breakdown Voltage	$I_C = 1\text{mA}$, $I_B = 0$	15	24	-	V
Collector-to-Substrate Breakdown-Voltage	$I_{C1} = 10\mu\text{A}$, $I_B = 0$, $I_E = 0$	20	60	-	V
Emitter-to-Base Breakdown Voltage (Note 3)	$I_E = 10\mu\text{A}$, $I_C = 0$	4	5.7	-	V
Collector-Cutoff-Current	$V_{CE} = 10\text{V}$, $I_B = 0$	-	-	0.5	μA
Collector-Cutoff-Current	$V_{CB} = 10\text{V}$, $I_E = 0$	-	-	40	nA
DC Forward-Current Transfer Ratio	$V_{CE} = 6\text{V}$	$I_C = 5\text{mA}$	35	88	-
		$I_C = 1\text{mA}$	40	90	-
		$I_C = 0.1\text{mA}$	35	85	-
Base-to-Emitter Voltage	$V_{CE} = 6\text{V}$	$I_C = 5\text{mA}$	0.71	0.81	0.91
		$I_C = 1\text{mA}$	0.66	0.76	0.86
		$I_C = 0.1\text{mA}$	0.60	0.70	0.80
Collector-to-Emitter Saturation Voltage	$I_C = 10\text{mA}$, $I_B = 1\text{mA}$	-	0.26	0.50	V
Magnitude of Difference in V_{BE}	Q_1 and Q_2 Matched	-	0.5	5	mV
Magnitude of Difference in I_B	$V_{CE} = 6\text{V}$, $I_C = 1\text{mA}$	-	0.2	3	μA
DYNAMIC CHARACTERISTICS					
Noise Figure	$f = 100\text{kHz}$, $R_S = 500\Omega$, $I_C = 1\text{mA}$	-	2.2	-	dB
Gain-Bandwidth Product	$V_{CE} = 6\text{V}$, $I_C = 5\text{mA}$	-	1.15	-	GHz
Collector-to-Base Capacitance	$V_{CB} = 6\text{V}$, $f = 1\text{MHz}$	-	See Fig. 5	-	pF
Collector-to-Substrate Capacitance	$V_{CI} = 6\text{V}$, $f = 1\text{MHz}$	-		-	pF
Emitter-to-Base Capacitance	$V_{BE} = 4\text{V}$, $f = 1\text{MHz}$	-		-	pF
Voltage Gain	$V_{CE} = 6\text{V}$, $f = 10\text{MHz}$, $R_L = 1\text{k}\Omega$, $I_C = 1\text{mA}$	-	28	-	dB
Power Gain	Cascode Configuration	27	30	-	dB
Noise Figure	$f = 100\text{MHz}$, $V_+ = 12\text{V}$, $I_C = 1\text{mA}$	-	3.5	-	dB
Input Resistance	Common-Emitter Configuration $V_{CE} = 6\text{V}$, $I_C = 1\text{mA}$, $f = 200\text{MHz}$	-	400	-	Ω
Output Resistance		-	4.6	-	k Ω
Input Capacitance		-	3.7	-	pF
Output Capacitance		-	2	-	pF
Magnitude of Forward Transadmittance		-	24	-	mS

NOTE:

3. When used as a zener for reference voltage, the device must not be subjected to more than 0.1mJ of energy from any possible capacitance or electrostatic discharge in order to prevent degradation of the junction. Maximum operating zener current should be less than 10mA.

Typical Performance Curves

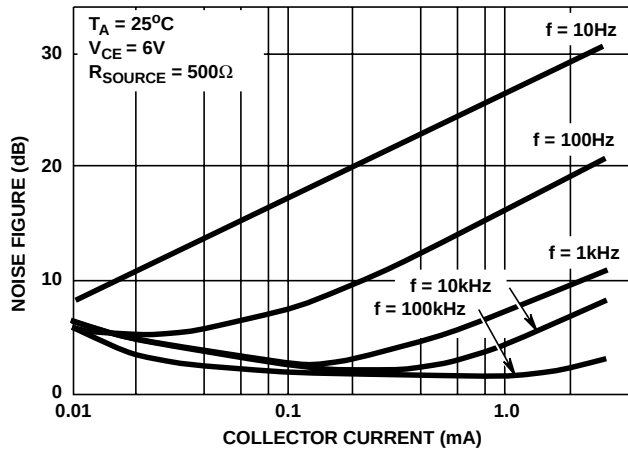


FIGURE 4. NOISE FIGURE vs COLLECTOR CURRENT

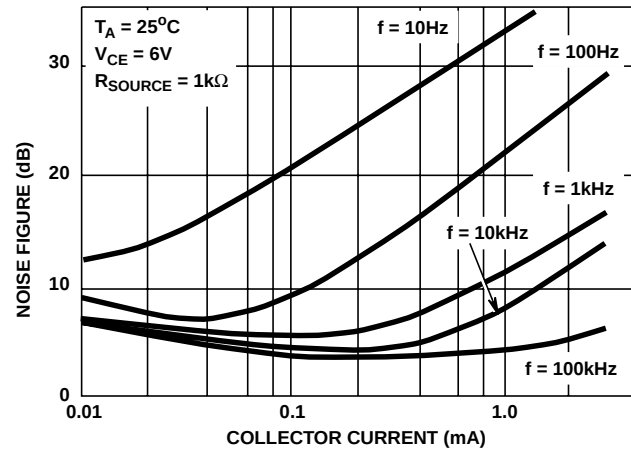


FIGURE 5. NOISE FIGURE vs COLLECTOR CURRENT

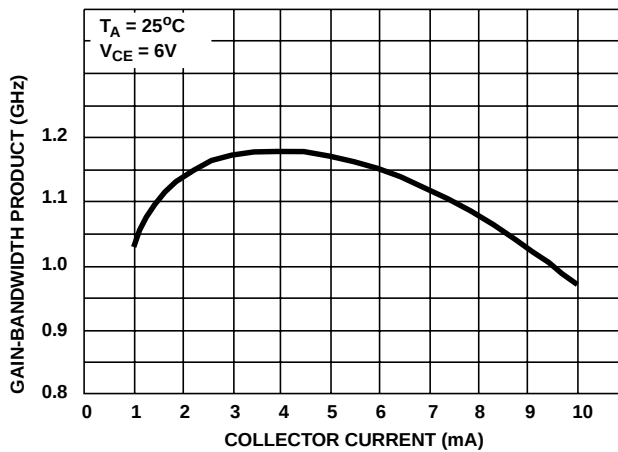


FIGURE 6. GAIN-BANDWIDTH PRODUCT vs COLLECTOR CURRENT

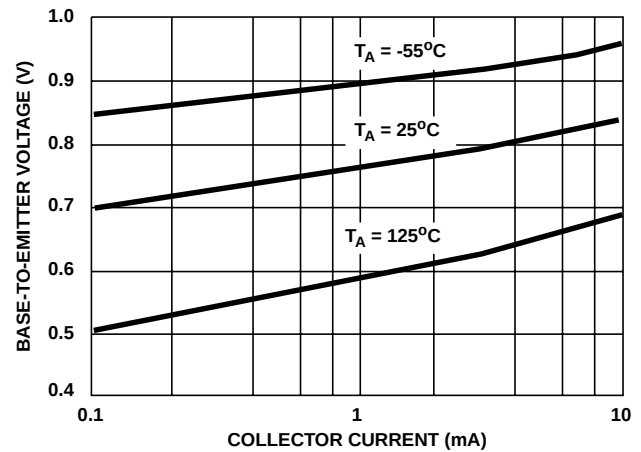
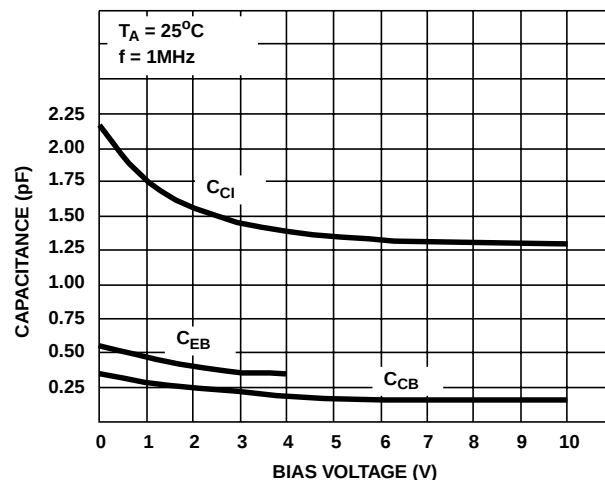


FIGURE 7. BASE-TO-EMITTER VOLTAGE vs COLLECTOR CURRENT

FIGURE 8A. CAPACITANCE vs BIAS VOLTAGE FOR Q₂

TRAN- SISTOR	CAPACITANCE (pF)							
	C _{CB}		C _{CE}		C _{EB}		C _{CI}	
	PKG	TOTAL	PKG	TOTAL	PKG	TOTAL	PKG	TOTAL
BIAS (V)	-	6V	-	6V	-	4V	-	6V
Q ₁	0.025	0.190	0.090	0.125	0.365	0.610	0.475	1.65
Q ₂	0.015	0.170	0.225	0.265	0.130	0.360	0.085	1.35
Q ₃	0.040	0.200	0.215	0.240	0.360	0.625	0.210	1.40
Q ₄	0.040	0.190	0.225	0.270	0.365	0.610	0.085	1.25
Q ₅	0.010	0.165	0.095	0.115	0.140	0.365	0.090	1.35

FIGURE 8B. TYPICAL CAPACITANCE VALUES AT f = 1MHz.
THREE TERMINAL MEASUREMENT. GUARD ALL
TERMINALS EXCEPT THOSE UNDER TEST.

Typical Performance Curves (Continued)

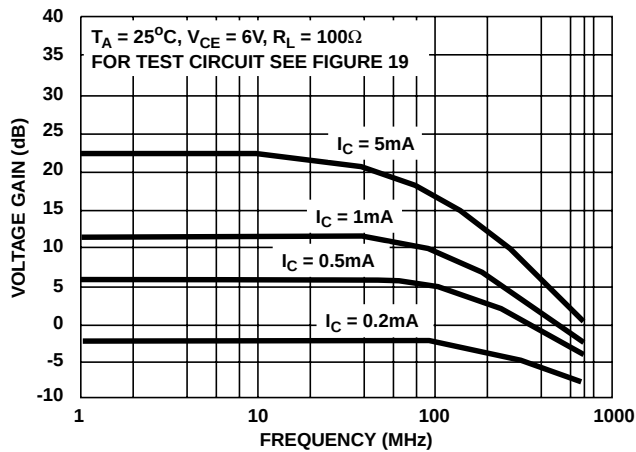


FIGURE 9. VOLTAGE GAIN vs FREQUENCY

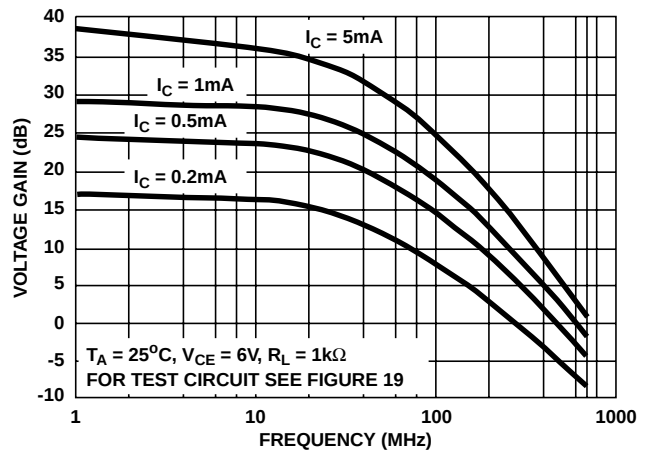
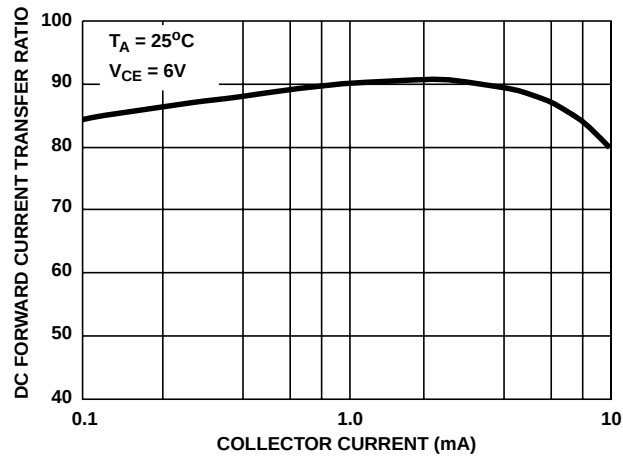
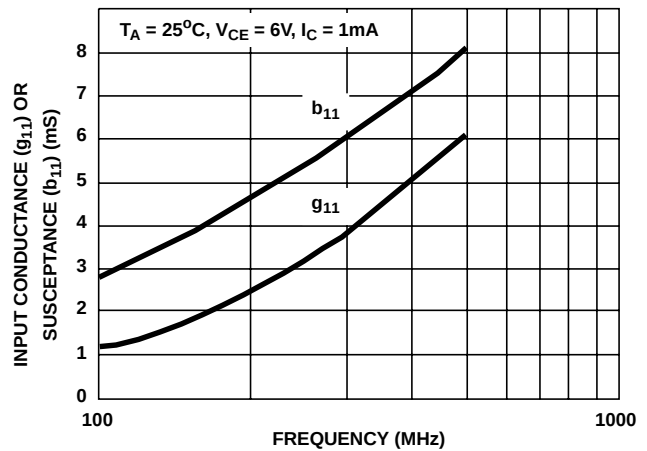
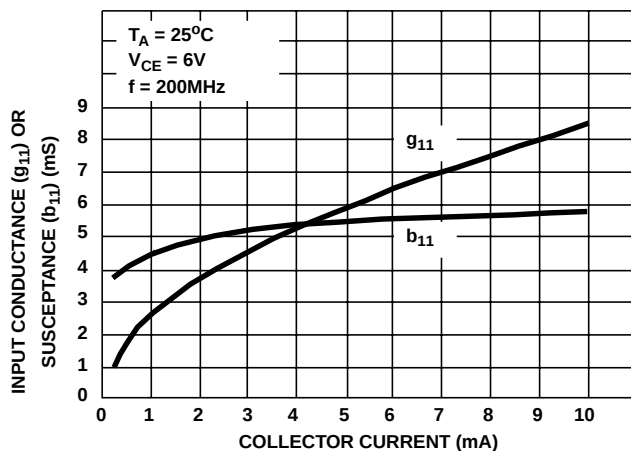
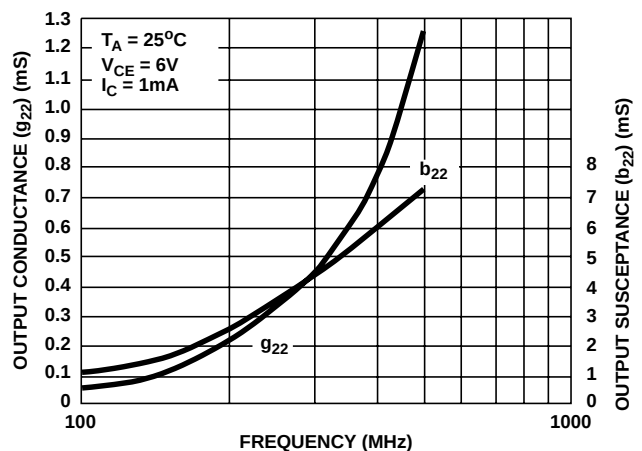
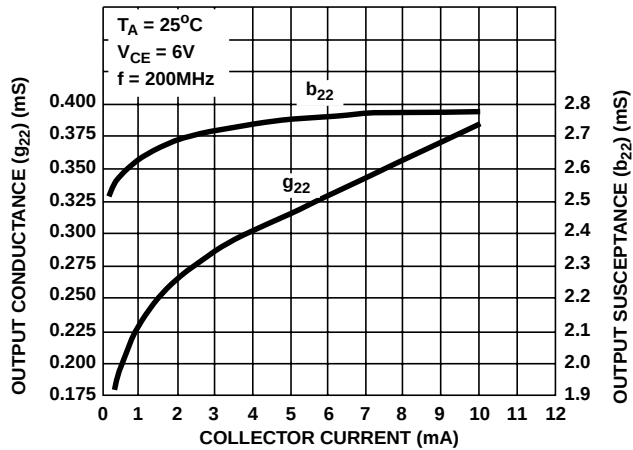
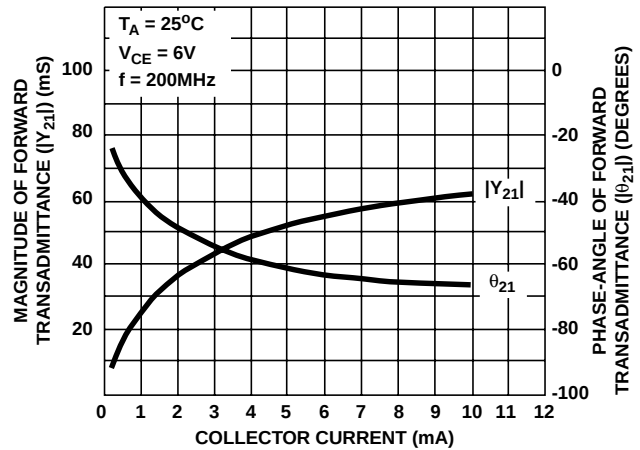
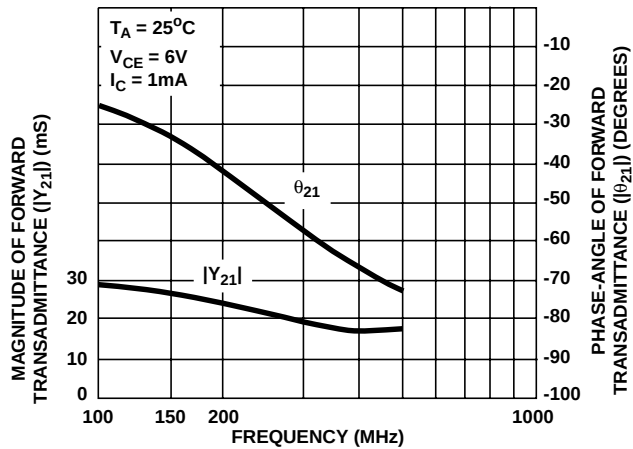
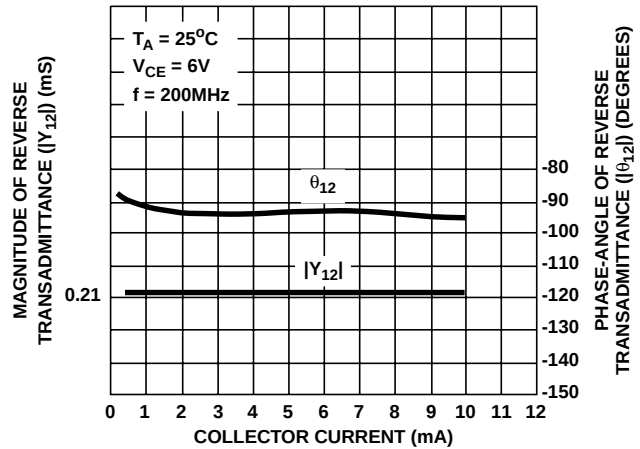
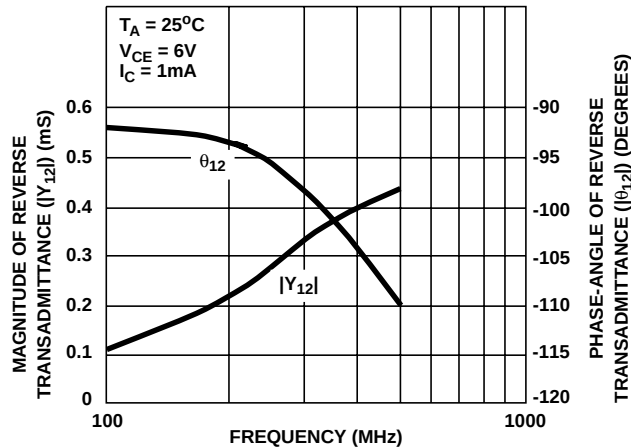


FIGURE 10. VOLTAGE GAIN vs FREQUENCY

FIGURE 11. DC FORWARD-CURRENT TRANSFER RATIO (h_{FE}) vs COLLECTOR CURRENTFIGURE 12. INPUT ADMITTANCE (Y_{11}) vs FREQUENCYFIGURE 13. INPUT ADMITTANCE (Y_{11}) vs COLLECTOR CURRENTFIGURE 14. OUTPUT ADMITTANCE (Y_{22}) vs FREQUENCY

Typical Performance Curves (Continued)

FIGURE 15. OUTPUT ADMITTANCE (Y_{22}) vs COLLECTOR CURRENTFIGURE 16. FORWARD TRANSADMITTANCE (Y_{21}) vs COLLECTOR CURRENTFIGURE 17. FORWARD TRANSADMITTANCE (Y_{21}) vs FREQUENCYFIGURE 18. REVERSE TRANSADMITTANCE (Y_{12}) vs COLLECTOR CURRENTFIGURE 19. REVERSE TRANSADMITTANCE (Y_{12}) vs FREQUENCY

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